KTC3072D/L

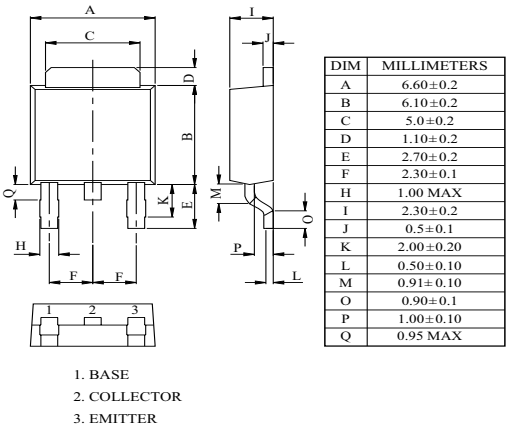
EPITAXIAL PLANAR NPN TRANSISTOR

HIGH CURRENT APPLICATION
CAMERA STROBO (For Electronic Flash Unit)

FEATURES

· Low Saturation Voltage : $V_{CE(sat)}$ = 0.4V(Max)(Ic=3A)

· High Performance at Low Supply Voltage.



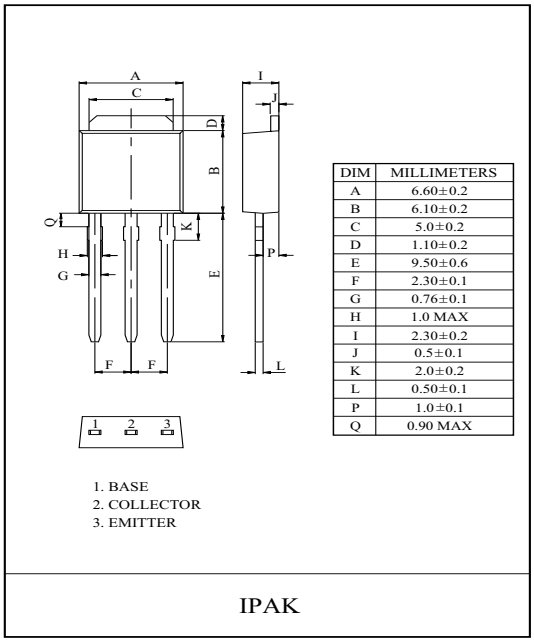
DIM	MILLIMETERS
A	6.60±0.2
B	6.10±0.2
C	5.0±0.2
D	1.10±0.2
E	2.70±0.2
F	2.30±0.1
H	1.00 MAX
I	2.30±0.2
J	0.5±0.1
K	2.00±0.20
L	0.50±0.10
M	0.91±0.10
O	0.90±0.1
P	1.00±0.10
Q	0.95 MAX

DPAK

MAXIMUM RATING (Ta=25℃)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Base Voltage		V_{CBO}	40	V
Collector-Emitter Voltage		V_{CEO}	20	V
Emitter-Base Voltage		V_{EBO}	7	V
Collector Current	DC	I_C	5	A
	Pulse (Note1)	I_{CP}	8	
Collector Power Dissipation		P_C	1.0	W
Junction Temperature		T_j	150	℃
Storage Temperature Range		T_{stg}	-55 ~ 150	℃

Note 1: Pulse Width ≦ 100mS, Duty Cycle ≦ 30%



DIM	MILLIMETERS
A	6.60±0.2
B	6.10±0.2
C	5.0±0.2
D	1.10±0.2
E	9.50±0.6
F	2.30±0.1
G	0.76±0.1
H	1.0 MAX
I	2.30±0.2
J	0.5±0.1
K	2.0±0.2
L	0.50±0.1
P	1.0±0.1
Q	0.90 MAX

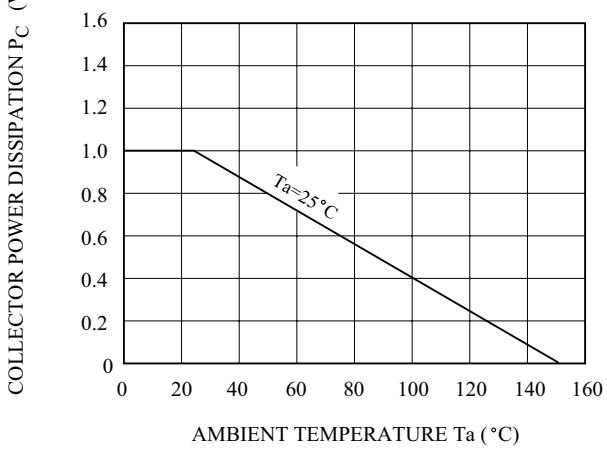
IPAK

ELECTRICAL CHARACTERISTICS (Ta=25℃)

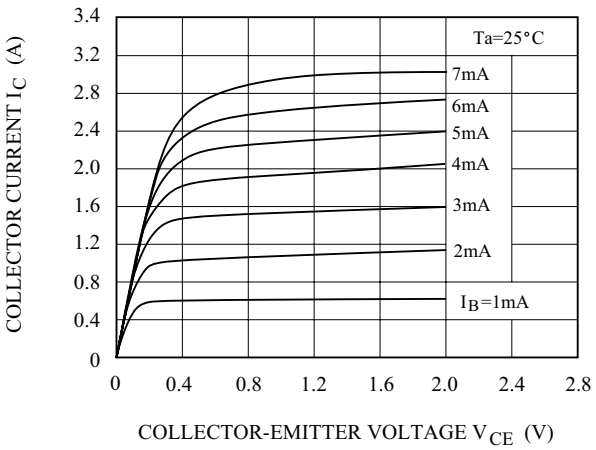
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Base Breakdown Voltage	$V_{(BR)CBO}$	I_C=100μA, I_E=0	40	-	-	V
Collector Emitter Breakdown Voltage (1)	$V_{(BR)CEO}$	I_C=1mA, I_B=0	20	-	-	V
Emitter Base Breakdown Voltage	$V_{(BR)EBO}$	I_E=10μA, I_C=0	7	-	-	V
Collector Cutoff Current	I_{CBO}	V_{CB}=20V, I_E=0	-	-	100	nA
Emitter Cutoff Current	I_{EBO}	V_{EB}=7V, I_C=0	-	-	100	nA
DC Current Gain	h_{FE}(1)(Note1)	V_{CE}=2V, I_C=0.5A	120	-	700	
	h_{FE}(2)	V_{CE}=2V, I_C=2A	100	-	-	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=3A, I_B=60mA(Pulse)	-	-	0.4	V
Transition Frequency	f_T	V_{CE}=6V, I_C=50mA	20	100	-	MHz
Collector Output Capacitance	C_{ob}	V_{CB}=20V, f=1MHz, I_E=0	-	-	50	pF

Note 1 : h_{FE}(1) Classification O:120 ~ 240, Y:200 ~ 400, GR:350 ~ 700

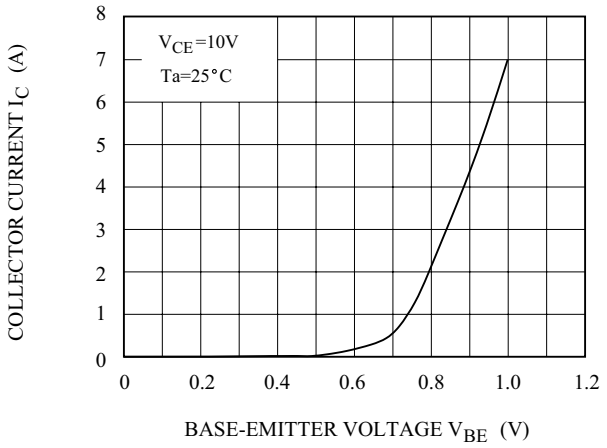
Pc - Ta



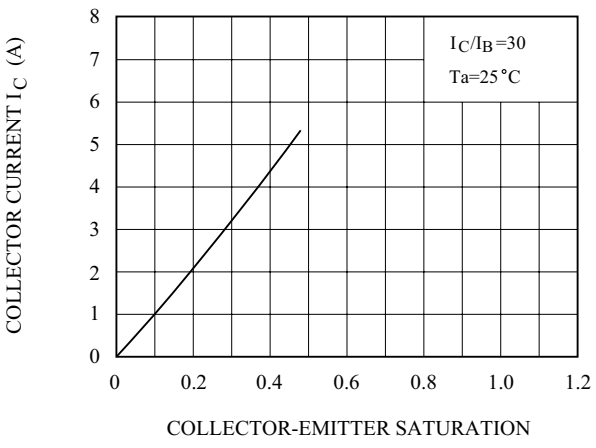
I_C - V_{CE}



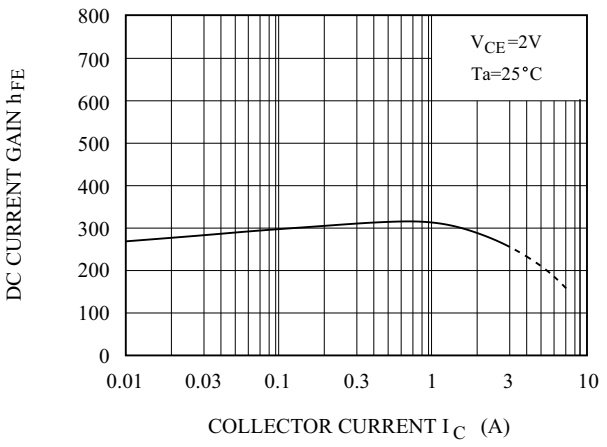
I_C - V_{BE}



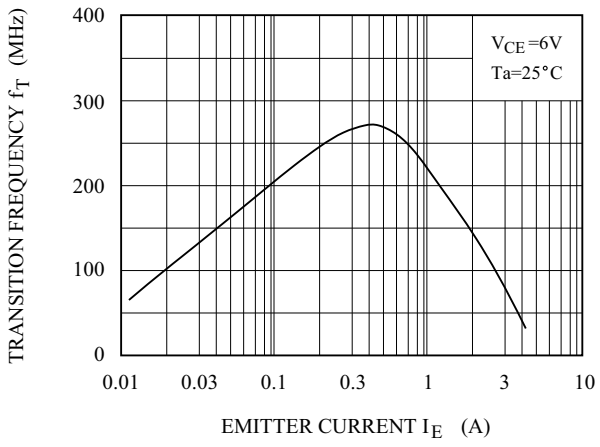
I_C - $V_{CE(sat)}$



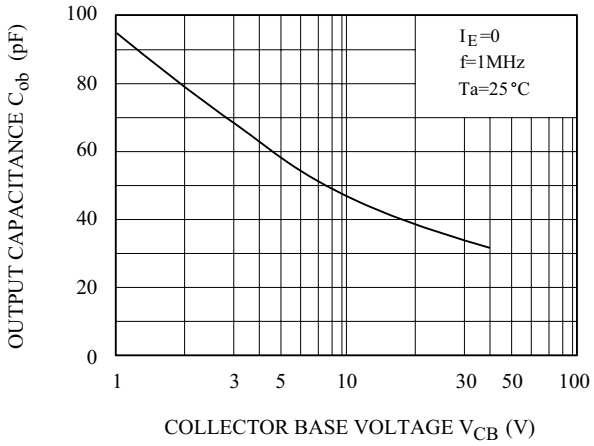
h_{FE} - I_C



f_T - I_E



C_{ob} - V_{CB}



SAFE OPERATION AREA